

## Dual P-channel Enhancement Mode Power MOSFET

### Features

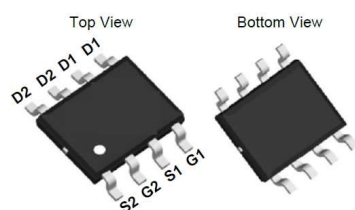
- $V_{DS} = -30V$ ,  $I_D = -9A$   
 $R_{DS(ON)} < 15m\Omega$  @  $V_{GS} = -10V$   
 $R_{DS(ON)} < 20m\Omega$  @  $V_{GS} = -4.5V$

### General Features

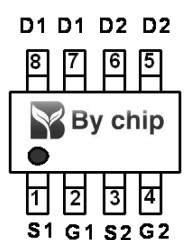
- Advanced Trench Technology
- Provide Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead Free and Green Available

100% UIS TESTED!

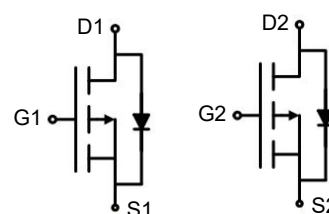
100%  $\Delta V_{ds}$  TESTED!



SOP-8 (Dual)



Pin assignment



Schematic diagram

### Absolute Maximum Ratings $T_C = 25^\circ C$ , unless otherwise noted

| Parameter                                        | Symbol         | Value      | Unit       |
|--------------------------------------------------|----------------|------------|------------|
| Drain-Source Voltage                             | $V_{DS}$       | -30        | V          |
| Continuous Drain Current                         | $I_D$          | -9         | A          |
| Pulsed Drain Current (note1)                     | $I_{DM}$       | -36        | A          |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$   | V          |
| Power Dissipation                                | $P_D$          | 1.4        | W          |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$ | -55 To 150 | $^\circ C$ |

### Thermal Resistance

| Parameter                               | Symbol     | Value | Unit         |
|-----------------------------------------|------------|-------|--------------|
| Thermal Resistance, Junction-to-Ambient | $R_{thJA}$ | 90    | $^\circ C/W$ |

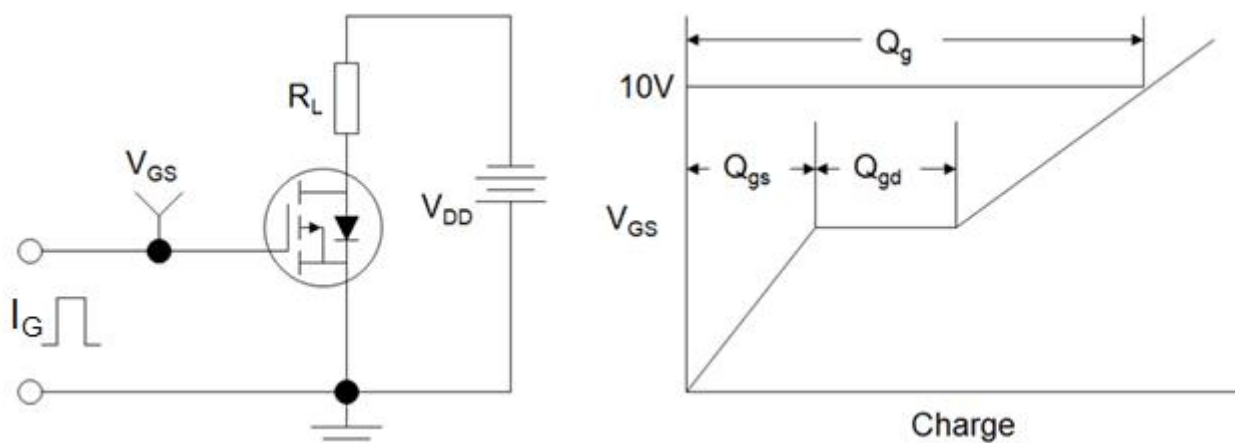
**Specifications**  $T_J = 25^{\circ}\text{C}$ , unless otherwise noted

| Parameter                               | Symbol               | Test Conditions                                                              | Value |      |      | Unit |
|-----------------------------------------|----------------------|------------------------------------------------------------------------------|-------|------|------|------|
|                                         |                      |                                                                              | Min.  | Typ. | Max. |      |
| Static Parameters                       |                      |                                                                              |       |      |      |      |
| Drain-Source Breakdown Voltage          | V <sub>(BR)DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA                                | -30   | --   | --   | V    |
| Zero Gate Voltage Drain Current         | I <sub>DSS</sub>     | V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V                                 | --    | --   | -1   | μA   |
| Gate-Source Leakage                     | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20V                                                       | --    | --   | ±100 | nA   |
| Gate-Source Threshold Voltage           | V <sub>GS(th)</sub>  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA                  | -1    |      | -3.0 | V    |
| Drain-Source On-Resistance              | R <sub>DS(on)</sub>  | V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A                                 | --    |      | 15   | mΩ   |
|                                         |                      | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5A                                | --    |      | 20   |      |
| Forward Transconductance                | g <sub>FS</sub>      | V <sub>DS</sub> = -5V, I <sub>D</sub> = -5A                                  | --    | 12   | --   | S    |
| Dynamic Parameters                      |                      |                                                                              |       |      |      |      |
| Input Capacitance                       | C <sub>iss</sub>     | V <sub>GS</sub> = 0V,<br>V <sub>DS</sub> = -4.5V,<br>f = 1.0MHz              | --    | 1786 | --   | pF   |
| Output Capacitance                      | C <sub>oss</sub>     |                                                                              | --    | 237  | --   |      |
| Reverse Transfer Capacitance            | C <sub>rss</sub>     |                                                                              | --    | 208  | --   |      |
| Total Gate Charge                       | Q <sub>g</sub>       | V <sub>DD</sub> = -15V,<br>I <sub>D</sub> = -4.5A,<br>V <sub>GS</sub> = -10V | --    | 18   | --   | nC   |
| Gate-Source Charge                      | Q <sub>gs</sub>      |                                                                              | --    | 3.4  | --   |      |
| Gate-Drain Charge                       | Q <sub>gd</sub>      |                                                                              | --    | 3    | --   |      |
| Turn-on Delay Time                      | t <sub>d(on)</sub>   | V <sub>DD</sub> = -15V,<br>I <sub>D</sub> = -4.5A,<br>R <sub>G</sub> = 1Ω    | --    | 6    | --   | ns   |
| Turn-on Rise Time                       | t <sub>r</sub>       |                                                                              | --    | 3    | --   |      |
| Turn-off Delay Time                     | t <sub>d(off)</sub>  |                                                                              | --    | 21   | --   |      |
| Turn-off Fall Time                      | t <sub>f</sub>       |                                                                              | --    | 3    | --   |      |
| Drain-Source Body Diode Characteristics |                      |                                                                              |       |      |      |      |
| Continuous Body Diode Current           | I <sub>S</sub>       | T <sub>C</sub> = 25°C                                                        | --    | --   | -9   | A    |
| Body Diode Voltage                      | V <sub>SD</sub>      | T <sub>J</sub> = 25°C, I <sub>SD</sub> = -5A, V <sub>GS</sub> = 0V           | --    | --   | -1.2 | V    |
| Reverse Recovery Charge                 | Q <sub>rr</sub>      | I <sub>F</sub> = -4.5A, V <sub>GS</sub> = 0V<br>di/dt=-500A/us               | --    | 13   | --   | nC   |
| Reverse Recovery Time                   | T <sub>rr</sub>      |                                                                              | --    | 8.5  | --   | ns   |

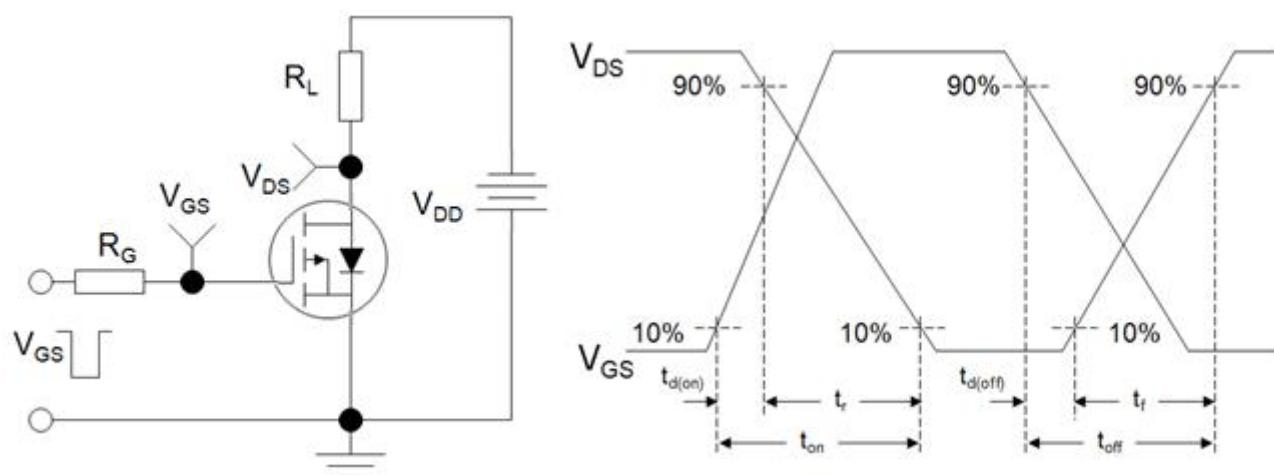
**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical  $R_G$

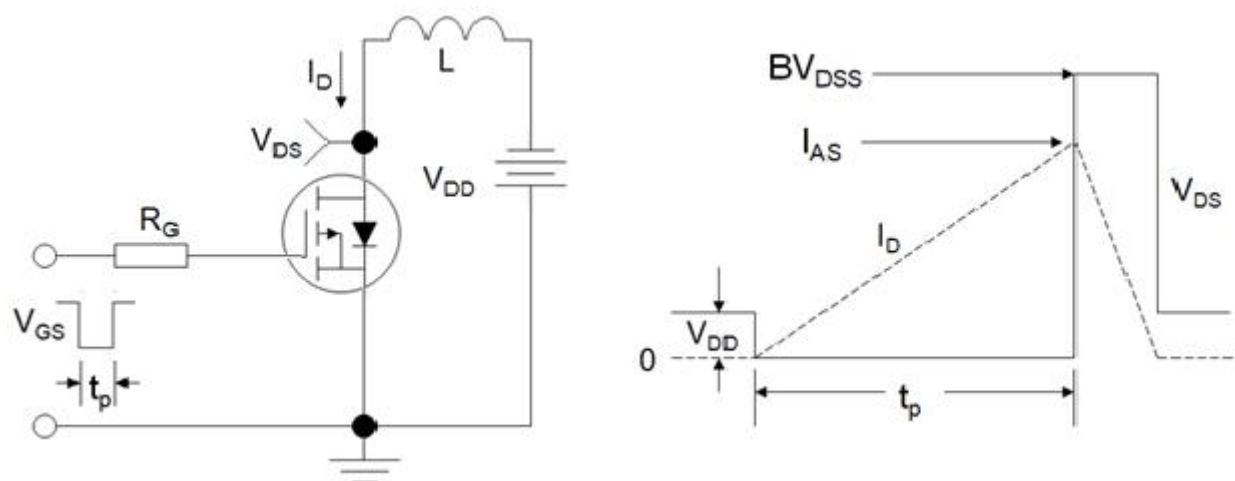
Gate Charge Test Circuit



Switch Time Test Circuit

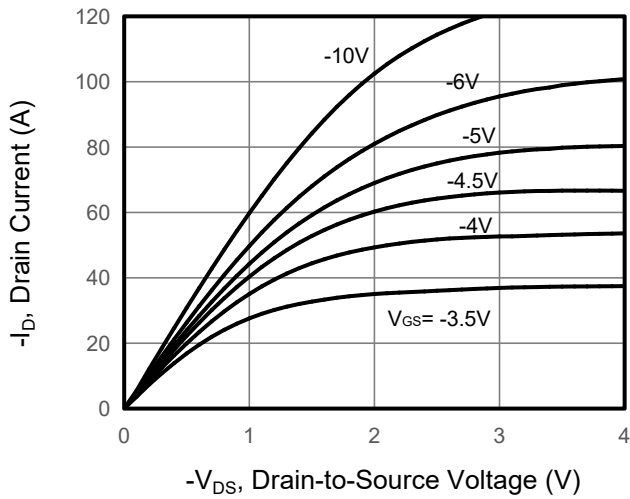


EAS Test Circuit

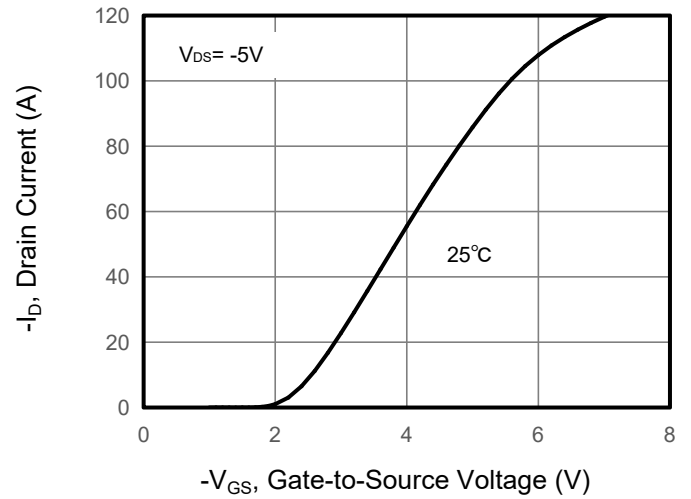


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

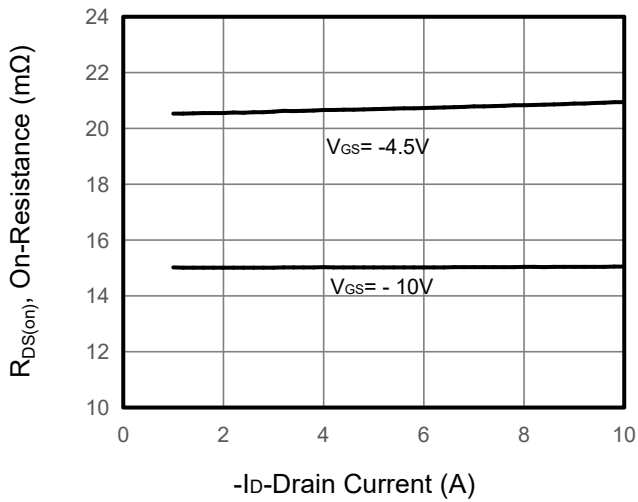
**Figure 1. Output Characteristics**



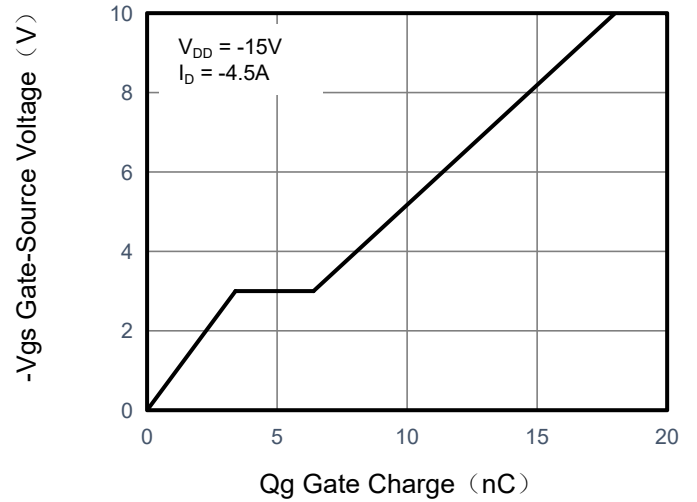
**Figure 2. Transfer Characteristics**



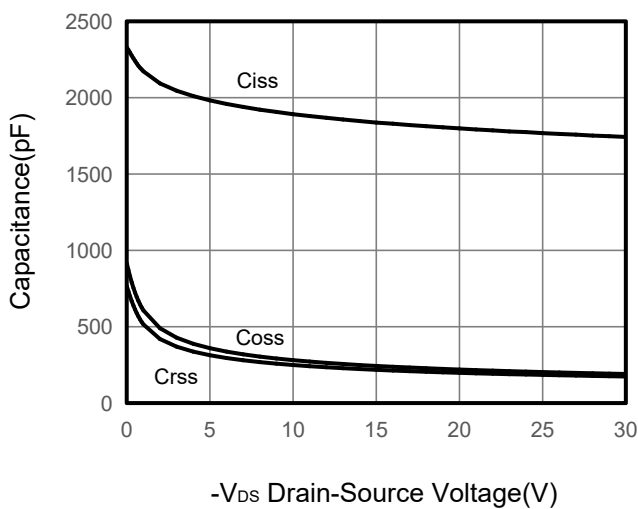
**Figure 3. Drain Source On Resistance**



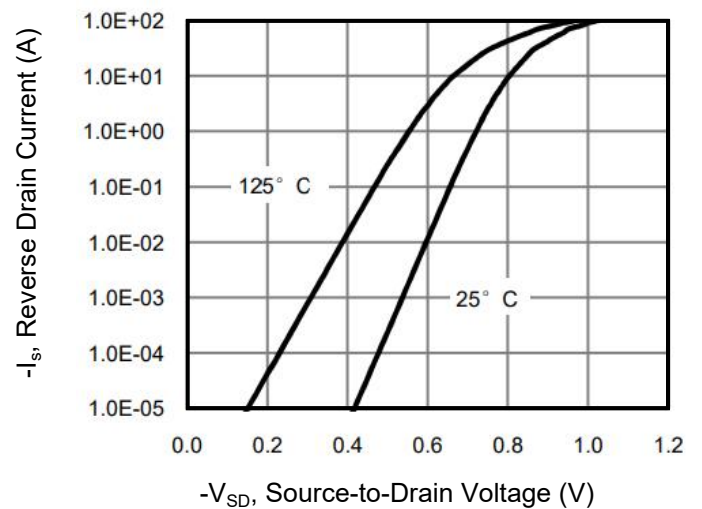
**Figure 4. Gate Charge**



**Figure 5. Capacitance**

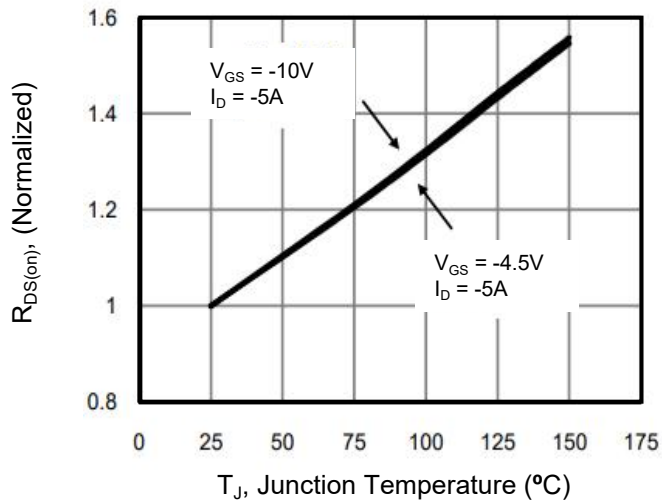


**Figure 6. Source-Drain Diode Forward**

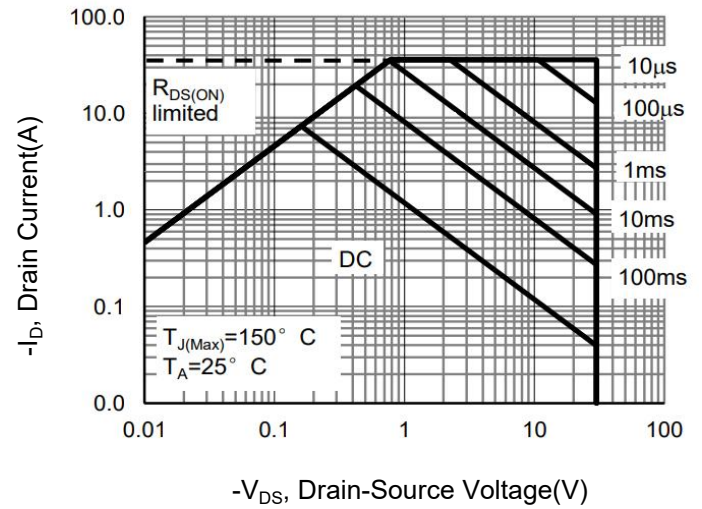


# Typical Characteristics $T_J = 25^\circ\text{C}$ , unless otherwise noted

## Figure 7. Drain-Source On-Resistance



## Figure 10. Safe Operation Area



## Figure 9. Normalized Maximum Transient Thermal Impedance

